L Number	Hits	Search Text	DB	Time stamp
391	261	low adj temperature adj polysilicon adj (tft or (thin adj film adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 20:39
392	76	(low adj temperature adj polysilicon adj (tft or (thin adj film adj transistor))) and buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 21:22
393	199	257/359.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 20:58
394	0	(low adj temperature adj polysilicon adj (tft or (thin adj film adj transistor))) and buffer and mounds	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 21:27
395	0	(low adj temperature adj polysilicon adj (tft or (thin adj film adj transistor))) and buffer and (surface adj roughness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 21:28
396	9	(low adj temperature adj polysilicon adj (tft or (thin adj film adj transistor))) and (surface adj roughness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 21:31
397	13	(low adj temperature adj polysilicon adj (tft or (thin adj film adj transistor))) and (recrystallization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 22:14
398	0	(low adj temperature adj polysilicon adj (tft or (thin adj film adj transistor))) and (second adj anneal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 22:15
399	0	(low adj temperature adj polysilicon adj (tft or (thin adj film adj transistor))) and (anneal adj polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 22:16
400	0	(low adj temperature adj polysilicon adj (tft or (thin adj film adj transistor))) and (recrystallization adj polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 22:16
401	0	(low adj temperature adj polysilicon adj (tft or (thin adj film adj transistor))) and (recrystallization near polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 22:16